	Application No.	Applicant(s)
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Notice of Allowability	10/723,517	WON ET AL.
Notice of Anowability	Examiner	Art Unit
	Michael Trinh	2822
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R	(OR REMAINS) CLOSED in this applied or other appropriate communication IGHTS. This application is subject to	plication. If not included will be mailed in due course. THIS
1. \boxtimes This communication is responsive to <u>Amendment and RCE</u>	E filed 12/15/06 & 11/14/05.	
2. The allowed claim(s) is/are <u>1-5,10,13-17 and 22</u> .		
 3. Acknowledgment is made of a claim for foreign priority ur a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 	e been received.	
Certified copies of the priority documents have	e been received in Application No	·
Copies of the certified copies of the priority do	cuments have been received in this	national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements
4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give		
5. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.	
(a) \square including changes required by the Notice of Draftspers	on's Patent Drawing Review (PTO-	948) attached
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in the C	office action of
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t		
6. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATERIAL n FOR THE DEPOSIT OF BIOLOGIC	nust be submitted. Note the AL MATERIAL.
		,
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	E [] Notice of Informal D	stant Application (DTO 450)
 Notice of Preferences Cited (P10-892) DNotice of Draftperson's Patent Drawing Review (PTO-948) 	6. ☐ Interview Summary	atent Application (PTO-152)
3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0	Paper No./Mail Dat	e
Paper No./Mail Date	_	
 Examiner's Comment Regarding Requirement for Deposit of Biological Material 		nt of Reasons for Allowance
	9.	That Sil
		Michael Trinin Primary Examinar

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DETAILED ACTION

*** This office action is in response to Applicant's RCE filed December 15, 2005 and Amendment submitted November 14, 2005. Claims are 1-5,10,13-17, and 22 are pending.

Allowable Subject Matter

- 1. Claims 1-5,10,13-17, and 22 are allowed.
- 2. The following is a statement of reasons for the indication of allowable subject matter:

Applicant's amendment and convincing remarks filed November 14, 2005 have overcome the rejections in the last office action. The references of record including Papasouliotis (6,846,745), Hanawa (5,753,044), etc., alone or in combination, do not fairly anticipatively disclose each and every aspect of the claimed high-density plasma CVD process, or fairly make a prima facie obvious case of the claimed process, in combination with other processing claimed limitations as recited in base claims 1 and 13, the inclusion of injecting first main process gases including a silicon source gas, an oxygen gas, a nitrogen free chemical gas and a hydrogen gas (helium gas also included the first main process gases of claim 13) into the process chamber to generate a high density plasma over the semiconductor substrate and to simultaneously form a silicon oxide layer on the semiconductor substrate; after injecting of the first main process gases, injecting second main process gases including a silicon source gas, an oxygen gas, a nitrogen free chemical gas, a hydrogen gas and a helium gas (helium gas not included the second main process gases of claim 13); and after injecting of the second main process gases, injecting third main process gases including a silicon source gas, an oxygen gas, and a hydrogen gas, wherein the semiconductor substrate is heated to a temperature in a range of about 550°C to about 700°C.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael M. Trinh whose telephone number is (571) 272-1847. The examiner can normally be reached on M-F: 9:00 Am to 5:30 Pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on (571) 272-2429. The central fax phone number is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

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applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). Oacs-102

Michael Trinin Primary Examiner